



TSM15N03PQ33

30V N-Channel Power MOSFET

PDFN33

8

Pin Definition:

1. Source	8. Drair
2. Source	7. Drair
3. Source	6. Drair
4. Gate	5. Drair

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
	12 @ V _{GS} =10V	7.8
30	17 @ V _{GS} =4.5V	7

Features

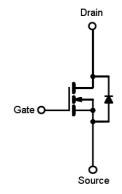
- Advanced Trench Technology
- Low On-Resistance
- Low gate charge typical @ 3.6nC (Typ.)
- Low Crss typical @ 38pF (Typ.)

Ordering Information

Part No.	Package	Packing		
TSM15N03PQ33 RGG	PDFN33	5Kpcs / 13" Reel		

Note: "G" denote for Halogen Free Product

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current	T _C =25℃		14		
	T _C =70℃	,	14	А	
	T _A =25℃	l _D	9.7		
	T _A =70℃		7.8		
Drain Current-Pulsed Note 1		I _{DM}	35	Α	
Avalanche Current, L=0.1mH		I _{AS} , I _{AR}	9	Α	
Avalanche Energy, L=0.1mH		E _{AS} , E _{AR}	4	mJ	
Maximum Power Dissipation	T _C =25℃		15.6		
	T _C =70℃	Б	10		
	T _A =25℃	P_{D}	3.2	W	
	T _A =70℃		2.1		
Storage Temperature Range		T _{STG}	-55 to +150	$\mathcal C$	
Operating Junction Temperature Range		T_J	-55 to +150	$\mathcal C$	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	8	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	40	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		4			•	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 7.8A$			9	12	mΩ
	$V_{GS} = 4.5V, I_D = 7A$	$R_{DS(ON)}$		13	17	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	1.2		2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge		Q_g		3.6		nC
Gate-Source Charge	$V_{DS} = 15V, I_D = 7.8A,$	Q_{gs}		1.2		
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		1		
Input Capacitance	\/ AF\/ \/ O\/	C _{iss}		415		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C _{oss}		90		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		38		
Switching						
Turn-On Delay Time		t _{d(on)}		13		
Turn-On Rise Time	$V_{GS} = 4.5V, V_{DS} = 15V,$	t _r		10		nS
Turn-Off Delay Time	$R_G = 1\Omega$	$t_{d(off)}$		11		113
Turn-Off Fall Time		t _f		8		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =6.3A	V_{SD}		0.8	1.3	V
Reverse Recovery Time	I _S = 6.3A, T _J =25 °C	t _{fr}		15		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q _{fr}		7		nC

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

3. The maximum current rating is limited by package.

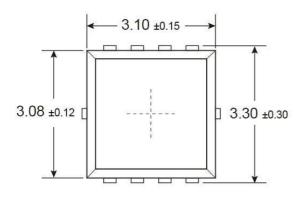


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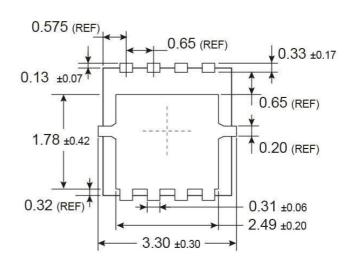
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PDFN33 Mechanical Drawing







Unit: Millimeters



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